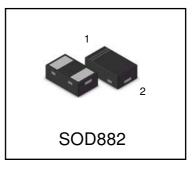


LESD8D8.0CT5G ESD PROTECTION DIODE

Discription

The LESD8D8.0CT5G is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.





▶◀

Ordering information

Marking

R8

--O 2

Shipping

10000/Tape&Reel

10-

Device

LESD8D8.0CT5G

S-LESD8D8.0CT5G



- I Small Body Outline Dimensions: 1.00 mm x 0.60 mm
- Low Body Height: 0.50 mm
- I Low Leakage
- I Response Time is Typically < 1 ns
- I ESD Rating of Class 3 per Human Body Model
- I IEC61000-4-2 Level 4 ESD Protection
- We declare that the material of product compliance with RoHS requirements.
- I S- prefix for automotive and other applications requiring unique site and control change requirements AEC-101 qualified and PPAP capable.

MAXIMUM BATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air Contact Contact discharge		±30 ±30	kV kV
Total Power Dissipation on FR-5 Board (Note 1)	PD	200	mW
@ T _A =25°C			
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	°C
Lead Solder Temperature – Maximum (10	TL	260	°C
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0*0.75*0.62 in.

Apr. 2019

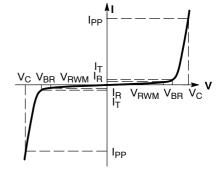


LESD8D8.0CT5G

Electrical Parameter

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter	
I _{PP}	Maximum Reverse Peak Pulse Current	
V _C	Clamping Voltage @ IPP	
V _{RWM}	Working Peak Reverse Voltage	
I _R	Maximum Reverse Leakage Current @ $\mathrm{V}_{\mathrm{RWM}}$	
V_{BR}	Breakdown Voltage @ I _T	
Ι _Τ	Test Current	
P _{pk}	Peak Power Dissipation	
С	Capacitance @ $V_R = 0$ and f = 1.0 MHz	

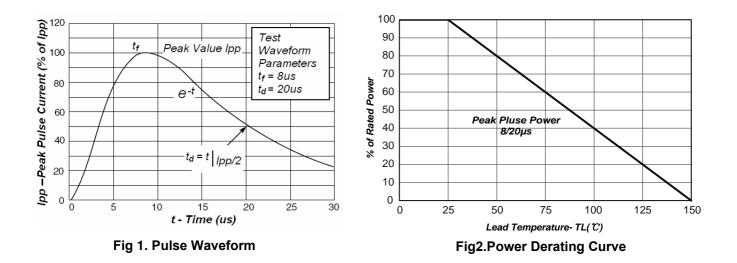


Electrical Parameter (T_A = 25°C unless otherwise noted)

Device	V _{RWM} (V)	I _R (μ Α) @ V _{RWM}		= (V) * = 1mA	I _{PP} (A)**	V _C (V) ** @ I _{PP} = 10A	Р _{РК} (W)**	C (pF) VR=0V, f=1MHz;
	Max	Max	Min	Max	Max	Max	Max	Тур.
LESD8D8.0CT5G	8	1	9	13	10	18	180	15

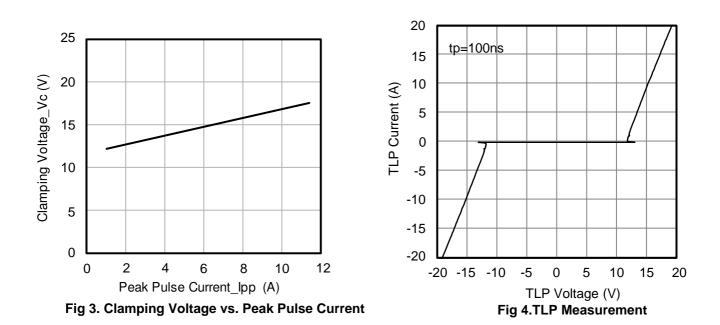
* V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

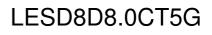
** Surge current waveform per Figure 1.



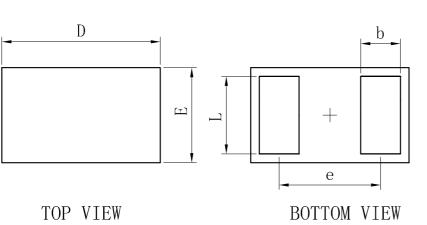


LESD8D8.0CT5G

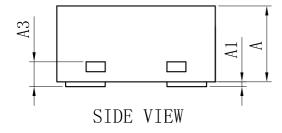




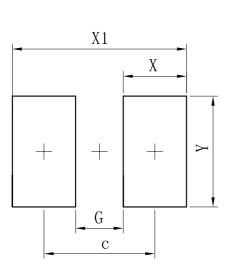
OUTLINE AND DIMENSIONS



SOD882				
Dim	Min	Тур	Max	
D	0.95	1.00	1.05	
Е	0.55	0.60	0.65	
е	-	0.64	-	
L	0.44	0.49	0.54	
b	0.20	0.25	0.30	
А	0.43	0.48	0.53	
A1	0	_	0.05	
A3	0.127REF.			
All Dimensions in mm				



SOLDERING FOOTPRINT



S0D882

SOD882

Dimensions	(mm)
с	0.70
G	0.30
Х	0.40
X1	1.10
Y	0.70

LRC

单击下面可查看定价,库存,交付和生命周期等信息

>>LRC(乐山无线电)